

Automotive P-Channel 80 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	- 80				
$R_{DS(on)}(\Omega)$ at V_{GS} = - 10 V	0.028				
I _D (A)	- 48				
Configuration	Single				



FEATURES

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET
- AEC-Q101 Qualifiedd
- 100 % R_q and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD50P08-28-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 80	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Dunio Comment	T _C = 25 °C	1	- 48		
Continuous Drain Current	T _C = 125 °C	- I _D	- 28		
Continuous Source Current (Diode Conduction) ^a		I _S	- 50	Α	
Pulsed Drain Current ^b		I _{DM}	- 190		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 45		
Single Pulse Avalanche Energy	L = 0.1 min	E _{AS}	100	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	T _C = 25 °C P _D	136	W	
	T _C = 125 °C	r D	45] vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R _{thJC}	1.1	O/ VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA		- 80	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		- 3.0	- 3.5	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		V _{GS} = 0 V	V _{DS} = - 80 V	-	-	- 1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 80 V, T _J = 125 °C	-	-	- 50	μΑ
		V _{GS} = 0 V	V _{DS} = - 80 V, T _J = 175 °C	-	-	- 250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} ≤ - 5 V	- 50	-	-	Α
Drain-Source On-State Resistance ^a		V _{GS} = - 10 V	I _D = - 12.5 A	-	0.023	0.028	
	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 12.5 A, T _J = 125 °C	-	-	0.049	Ω
		V _{GS} = - 10 V	I _D = - 12.5 A, T _J = 175 °C	-	-	0.061	
Forward Transconductanceb	9 _{fs}	V _{DS} = - 15 V, I _D = - 12.5 A		-	32	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	4826	6035	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{GS} = 0 \text{ V}$ $V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$	-	343	430	pF
Reverse Transfer Capacitance	C _{rss}			-	224	280	
Total Gate Charge ^c	Qg			-	95	145	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -40 \text{ V}, I_{D} = -12.5 \text{ A}$	-	19	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	26		
Gate Resistance	R _g	f = 1 MHz		1.73	3.47	5.21	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	15	23	
Rise Time ^c	t _r	$V_{DD} = \text{- }40 \text{ V}, \text{ R}_{L} = 3.8 \Omega$ $I_{D} \cong \text{- }10.5 \text{ A}, \text{ V}_{GEN} = \text{- }10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	11	17	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	65	98	
Fall Time ^c	t _f			-	16	24	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	- 190	Α
Forward Voltage	V_{SD}	I _F = - 10 A, V _{GS} = 0		_	- 0.82	- 1.5	V

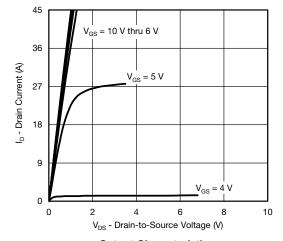
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

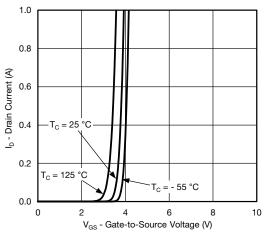
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



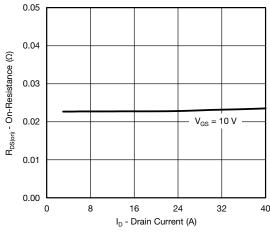
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



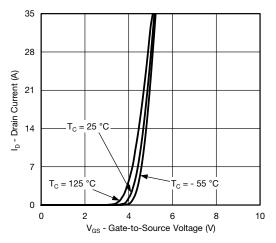
Output Characteristics



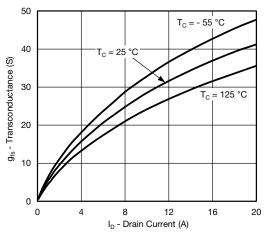
Transfer Characteristics



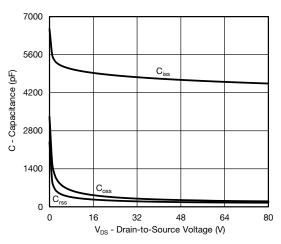
On-Resistance vs. Drain Current



Transfer Characteristics



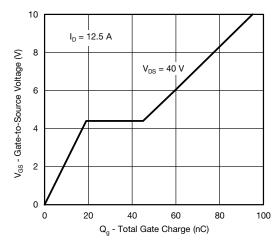
Transconductance



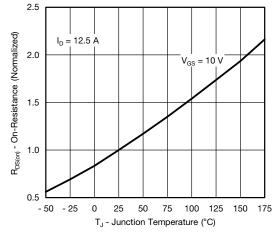
Capacitance



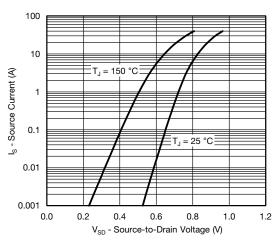
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



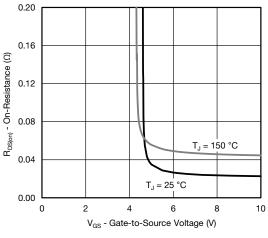
Gate Charge



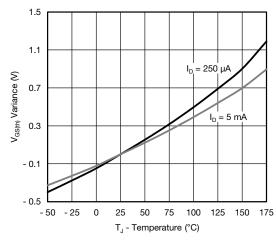
On-Resistance vs. Junction Temperature



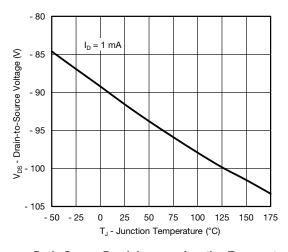
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



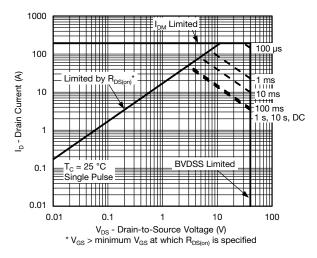
Threshold Voltage



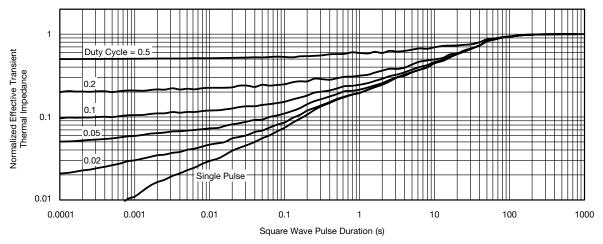
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25 \, ^{\circ}C$, unless otherwise noted)



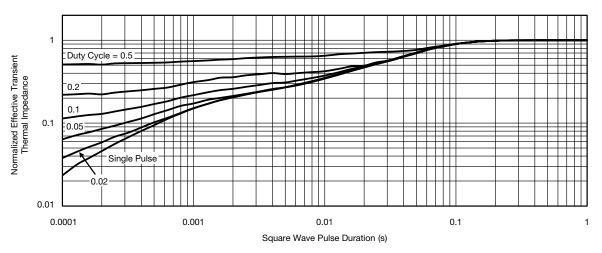
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

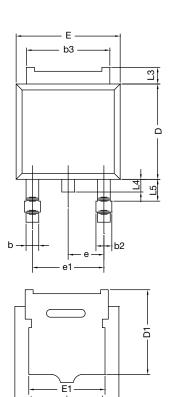
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

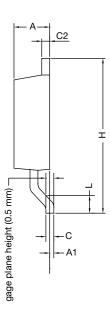
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TO-252AA Case Outline





	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13					

DWG: 6019

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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